

N-channel 30 V 2.8mΩ logic level MOSFET in LFPAK using NextPower technology

Rev. 01 — 2 May 2011

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance

### **1.3 Applications**

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

### 1.4 Quick reference data

### Table 1. Quick reference data

 Optimised for 4.5V Gate drive utilising NextPower Superjunction technology

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- Ultra low QG, QGD, and QOSS for high system efficiencies at low and high loads
- Power OR-ing
- Server power supplies
- Sync rectifier

Table 1.	Quick reference da	ta					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <u>Figure 1</u>	[1]	-	-	100	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	106	W
Tj	junction temperature			-55	-	175	°C
Static ch	aracteristics						
$R_{DSon}$	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 4.5 \; V;  I_D = 25 \; A;  T_j = 25 \; ^\circ C; \\ \text{see } \overline{Figure \; 12} \end{array}$		-	3.1	3.65	mΩ
		$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \text{ T}_{j} = 25 \text{ °C};$ see Figure 12		-	2.35	2.8	mΩ

### N-channel 30 V 2.8mΩ logic level MOSFET in LFPAK using NextPower

Table 1.	QUICK reference d	atacontinued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
Q <sub>GD</sub>	gate-drain charge	$\label{eq:VGS} \begin{array}{l} V_{GS} = 4.5 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ V_{DS} = 15 \text{ V}; \text{ see } \underline{\text{Figure } 14}; \\ \text{see } \underline{\text{Figure } 15} \end{array}$	-	5.5	-	nC
Q <sub>G(tot)</sub>	total gate charge	$\label{eq:VGS} \begin{array}{l} V_{GS} = 4.5 \; V; \; I_{D} = 25 \; A; \\ V_{DS} = 15 \; V; \; see \; \underline{Figure \; 14}; \\ see \; \underline{Figure \; 15} \end{array}$	-	18	-	nC

 Table 1.
 Quick reference data ...continued

[1] Continuous current is limited by package.

### 2. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		5
2	S	source	mb	
3	S	source		
4	G	gate	a ;	
mb	D	mounting base; connected to drain	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	mbb076 S

#### SOT669 (LFPAK; Power-SO8)

### 3. Ordering information

Table 3.	Ordering in	ring information		
Type numb	ber	Package		
		Name	Description	Version
PSMN2R6-	30YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

### 4. Marking

Table 4. Marking codes	
Type number	Marking code <sup>[1]</sup>
PSMN2R6-30YLC	2C630L

[1] % = placeholder for manufacturing site code

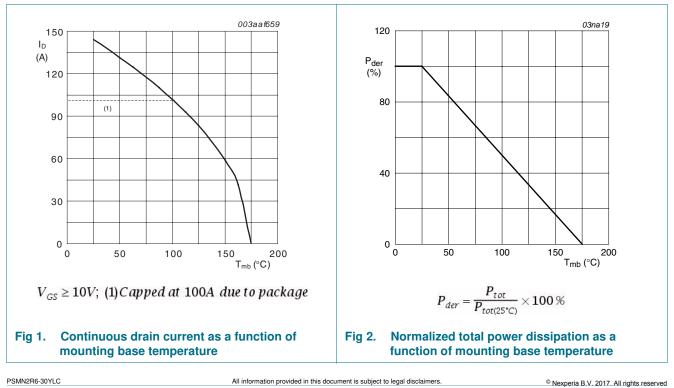
### 5. Limiting values

#### Table 5. Limiting values

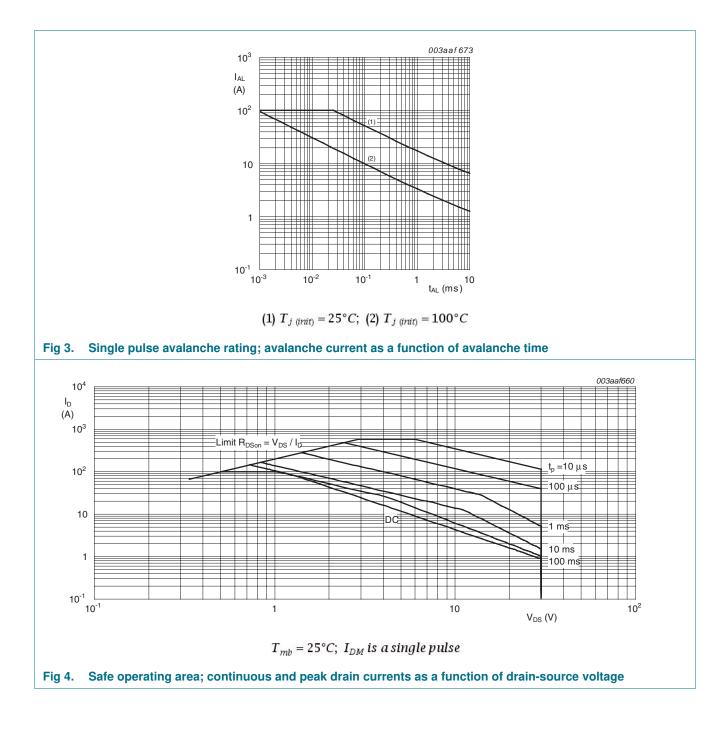
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	30	V
V <sub>DGR</sub>	drain-gate voltage	25 °C $\leq$ T <sub>j</sub> $\leq$ 175 °C; R <sub>GS</sub> = 20 k $\Omega$	-	30	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	<u>[1]</u> _	100	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	<u>[1]</u> _	100	А
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; see <u>Figure 4</u>	-	575	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	106	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
V <sub>ESD</sub>	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	460	-	V
Source-drain	n diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	96	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	575	А
Avalanche r	uggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(\text{init})} = 25 \; ^{\circ}\text{C}; \; I_{D} = 100 \; A; \\ V_{sup} \leq 30 \; V; \; R_{GS} = 50 \; \Omega; \; unclamped; \\ see \; \underline{Figure 3} \end{array}$	-	50	mJ

[1] Continuous current is limited by package.



# PSMN2R6-30YLC



#### **Thermal characteristics** 6.

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 5	-	1.25	1.42	K/W



## 7. Characteristics

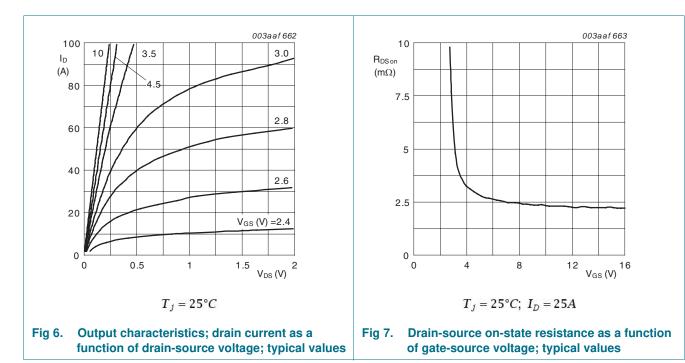
Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	30	-	-	V
	voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	1.05	1.54	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ	
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
		$V_{GS}$ = -16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
R <sub>DSon</sub> drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 4.5 \; V; \; I_D = 25 \; A; \; T_j = 25 \; ^\circ C; \\ \text{see } \underline{Figure \; 12} \end{array}$	-	3.1	3.65	mΩ	
	$V_{GS}$ = 4.5 V; $I_D$ = 25 A; $T_j$ = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	6.05	mΩ	
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 12</u>	-	2.35	2.8	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	4.65	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	0.96	1.92	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub> total gate charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	39	-	nC	
		$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	18	-	nC
		$I_D = 0 \; A;  V_{DS} = 0 \; V;  V_{GS} = 10 \; V$	-	36	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	6.1	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	see Figure 14; see Figure 15	-	3.9	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	2.2	-	nC
Q <sub>GD</sub>	gate-drain charge		-	5.5	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15};$	-	2.73	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2435	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{100}$	-	549	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	178	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; $R_L$ = 0.6 Ω; $V_{GS}$ = 4.5 V;	-	35	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \ \Omega$	-	24	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	42	-	ns
t <sub>f</sub>	fall time		-	37	-	ns

# PSMN2R6-30YLC

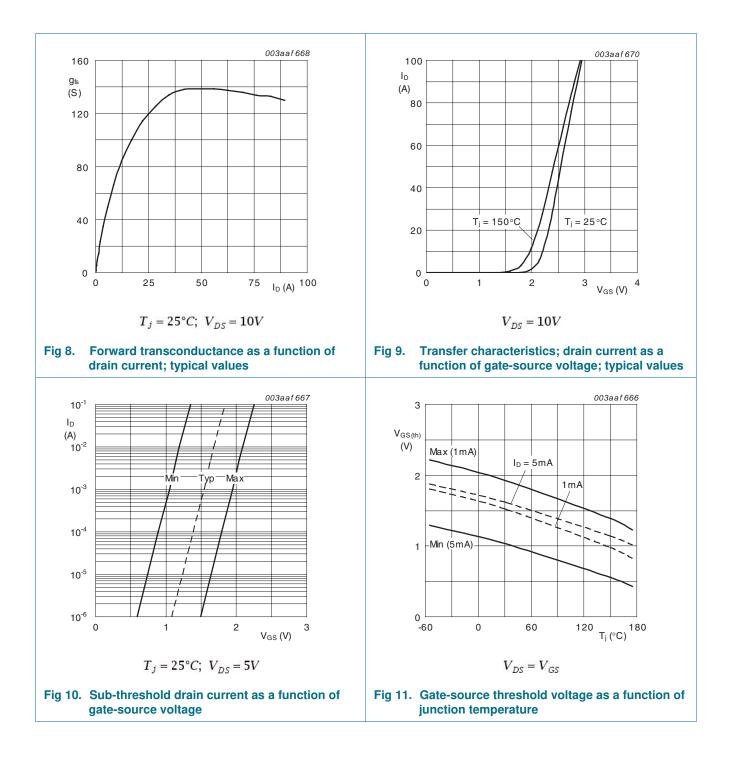
### N-channel 30 V 2.8mΩ logic level MOSFET in LFPAK using NextPower

#### Table 7. Characteristics ...continued

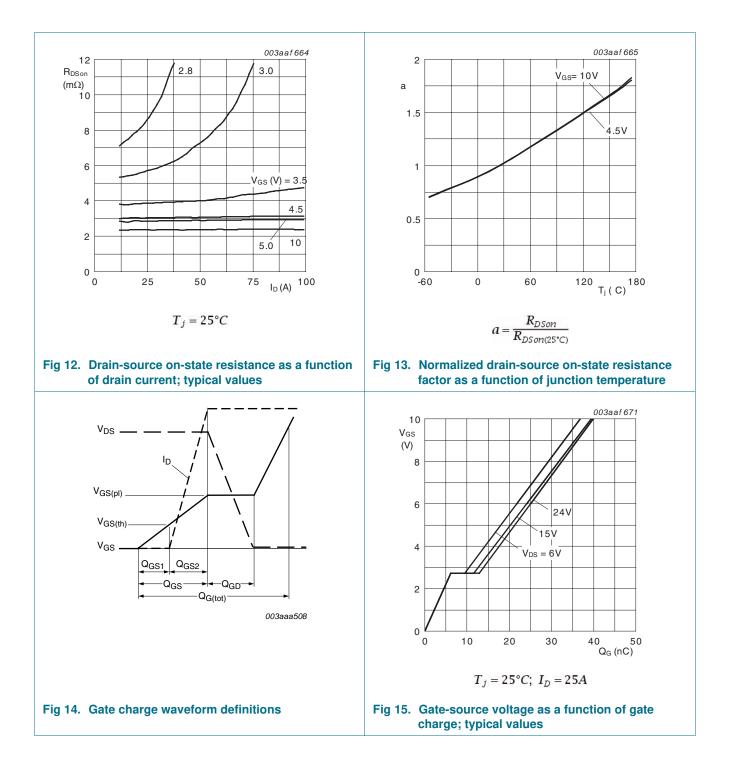
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Q <sub>oss</sub>	output charge	$V_{GS}$ = 0 V; $V_{DS}$ = 15 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	17	-	nC
Source-dra	in diode					
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 17</u>	-	0.8	1.1	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs;	-	33	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 V; V_{DS} = 15 V$	-	31	-	nC
t <sub>a</sub>	reverse recovery rise time	$V_{GS} = 0 V; I_S = 25 A;$	-	20	-	ns
t <sub>b</sub>	reverse recovery fall time	dl <sub>S</sub> /dt = -100 A/µs; V <sub>DS</sub> = 15 V; see <u>Figure 18</u>	-	13	-	ns



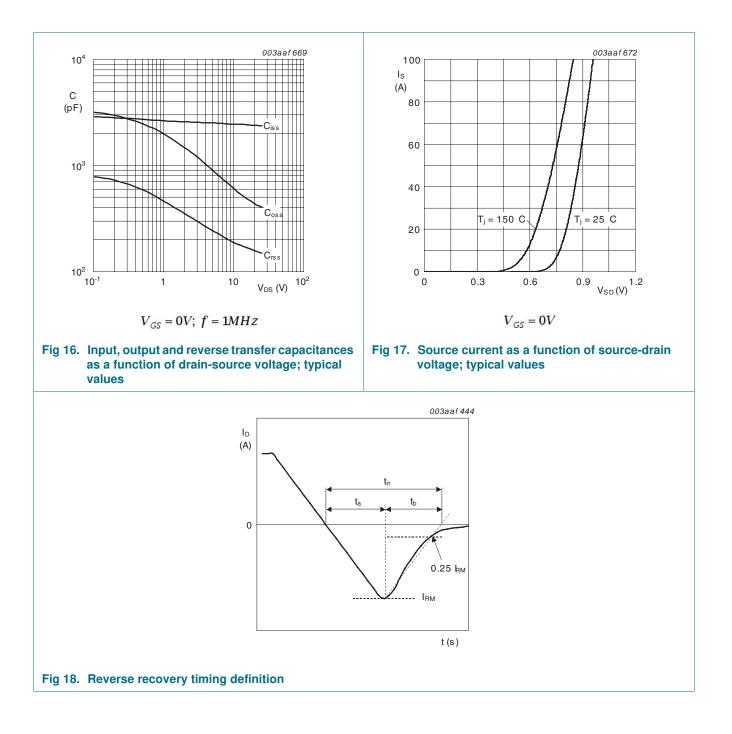
# PSMN2R6-30YLC



# PSMN2R6-30YLC

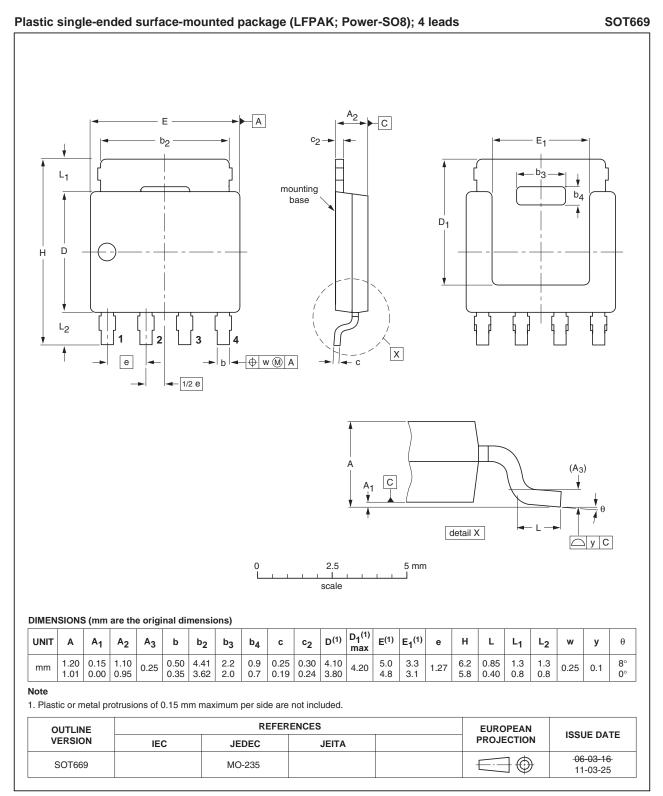


# PSMN2R6-30YLC



#### N-channel 30 V 2.8mΩ logic level MOSFET in LFPAK using NextPower

### 8. Package outline



#### Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

PSMN2R6-30YLC Product data sheet

# 9. Revision history

Table 8. Revision h	Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
PSMN2R6-30YLC v.1	20110502	Product data sheet	-	-		

### **10. Legal information**

### 10.1 Data sheet status

Document status [1] [2]	Product status 3	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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### 12. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Marking2
5	Limiting values
6	Thermal characteristics5
7	Characteristics6
8	Package outline11
9	Revision history12
10	Legal information13
10.1	Data sheet status
10.2	Definitions
10.3	Disclaimers
10.4	Trademarks14
11	Contact information14